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TITLE : SEMICONDUCTOR WAFER

ABSTRACT : PURPOSE: To increase the yield of the wafer by a method wherein the surface roughness of the surface of the wafer part is set at  $0.07\mu\text{m}$  or less in Ra value (center line average height).

CONSTITUTION: An etchant is supplied to a stacked body of a plurality of silicon wafers; the surface of its chamfered part is brought into contact with the etchant. The time of this contact is set normally at about 30 to 120 seconds. For example, an etchant within a range of  $\text{HF}:\text{HNO}_3=1:2$  to 5 is used as the etchant. As a result, the chamfered part of the silicon wafers is etched sufficiently, and the surface roughness of its etched face is set to  $0.07\mu\text{m}$  or lower in an Ra value (central-line mean value). Thereby, it is possible to reduce that a slip is caused due to the thermal stress of semiconductor wafers.

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